

Photoluminescence studies of the futuristic SnSe semiconductor



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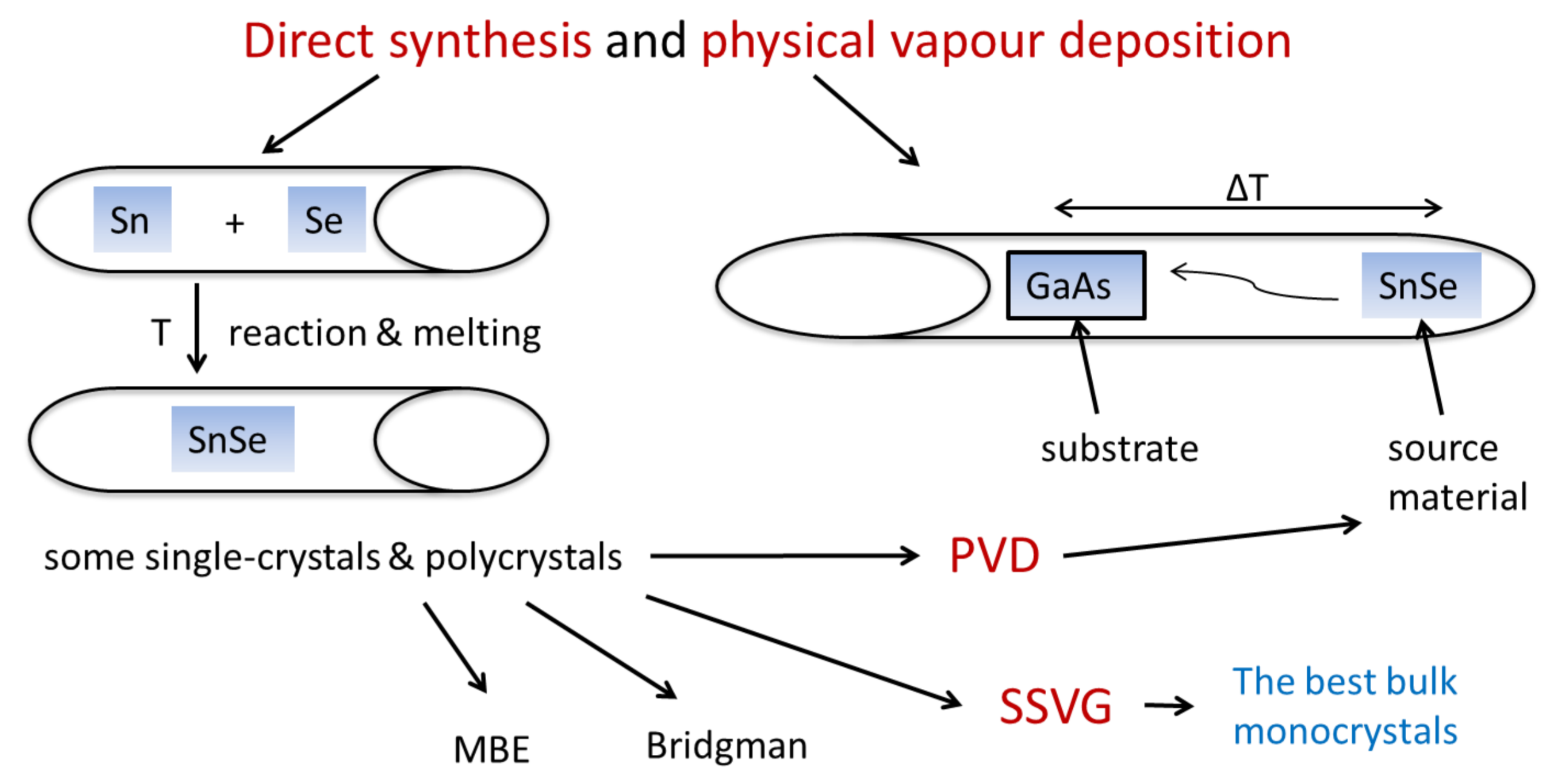
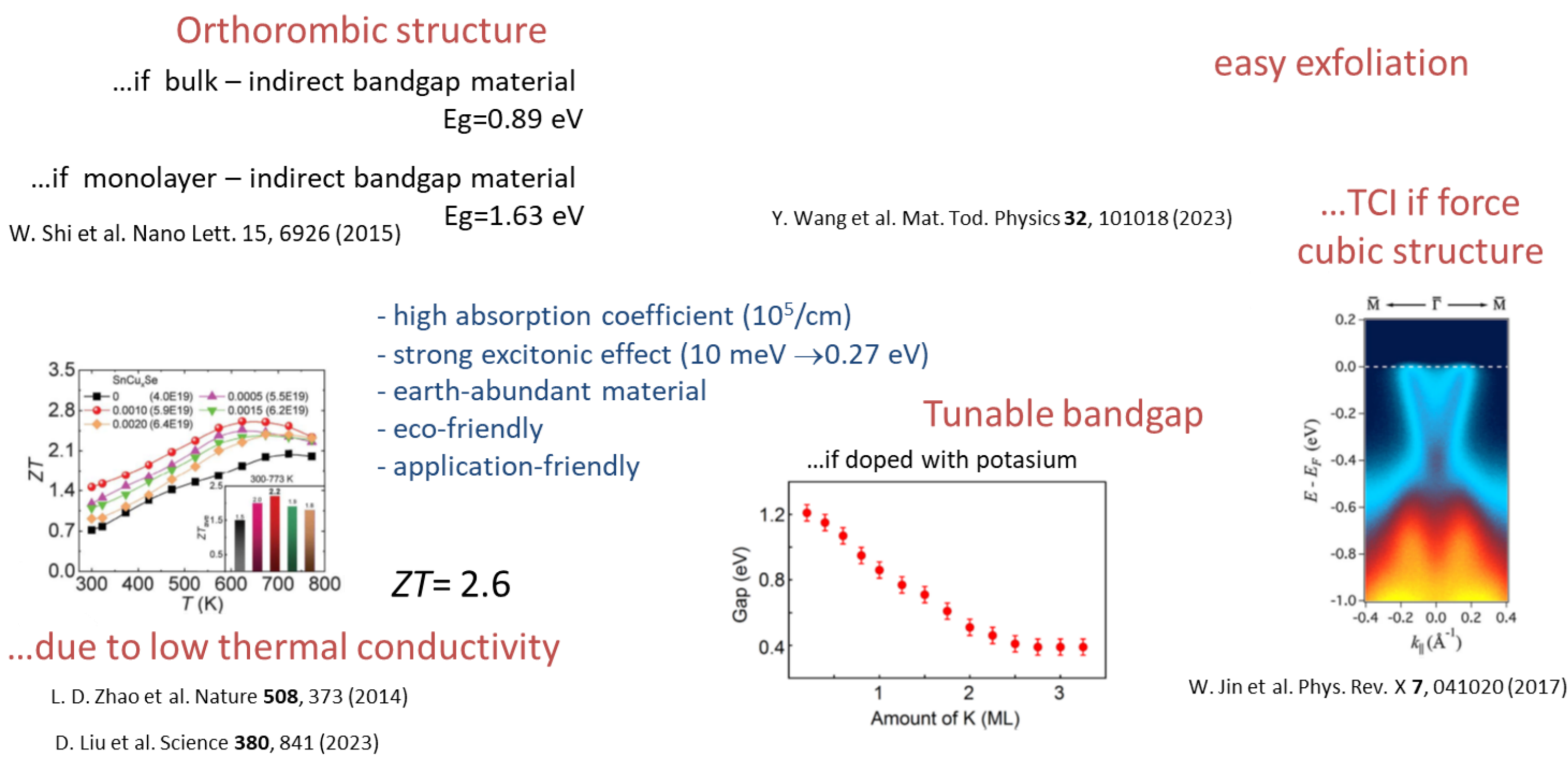
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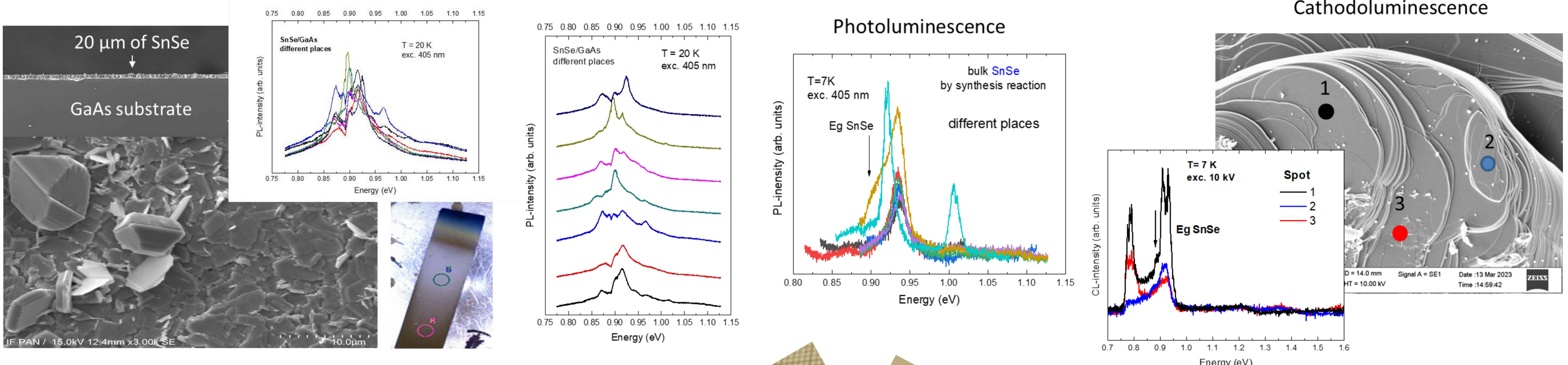
... about SnSe

Growth methods we used



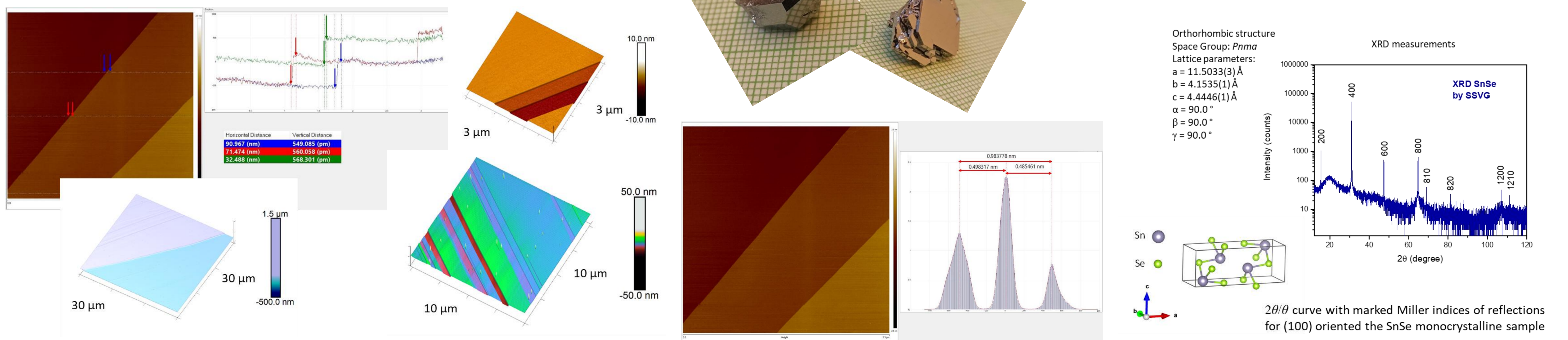
SnSe by physical vapour deposition – photoluminescence

SnSe by direct synthesis - photo- and cathodoluminescence vs position



SnSe by SSVG- AFM characterization

SnSe monocrystals by SSVG - XRD characterization



SnSe by SSVG – photo - and cathodoluminescence vs temperature

SnSe by SSVG – luminescence summary and interpretation

